

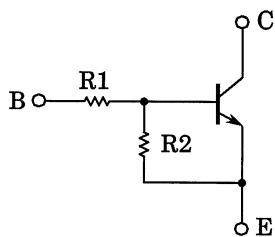
TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

RN1321A,RN1322A,RN1323A,RN2324A RN1325A,RN1326A,RN1327A

Switching, Inverter Circuit, Interface Circuit
And Driver Circuit Applications

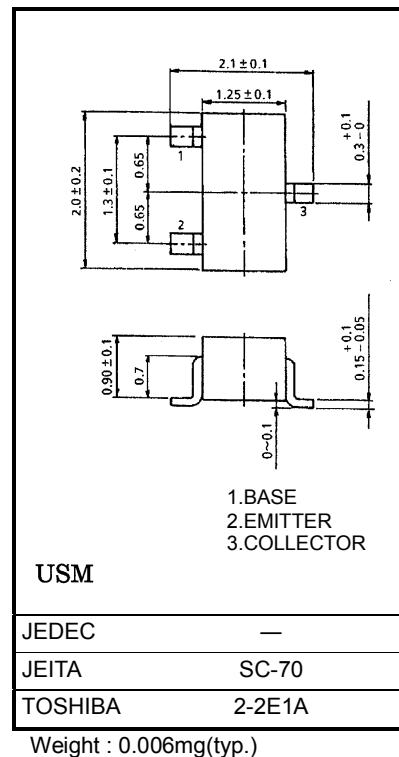
- High current driving is possible.
- Since bias resistors are built in the transistor, the miniaturization of the apparatus by curtailment of the number of parts and laborsaving of an assembly are possible.
- Many kinds of resistance value are lined up in order to support various kinds of circuit design.
- Complementary to RN2321A~RN2327A
- Low $V_{CE(sat)}$ enable to be low power dissipation on high current driving.

Equivalent Circuit And Bias Resistance Values



Type No.	R1 (kΩ)	R2 (kΩ)
RN1321A	1	1
RN1322A	2.2	2.2
RN1323A	4.7	4.7
RN1324A	10	10
RN1325A	0.47	10
RN1326A	1	10
RN1327A	2.2	10

Unit in mm

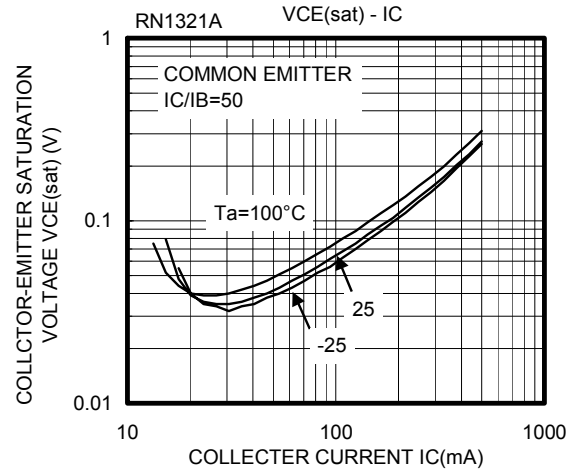
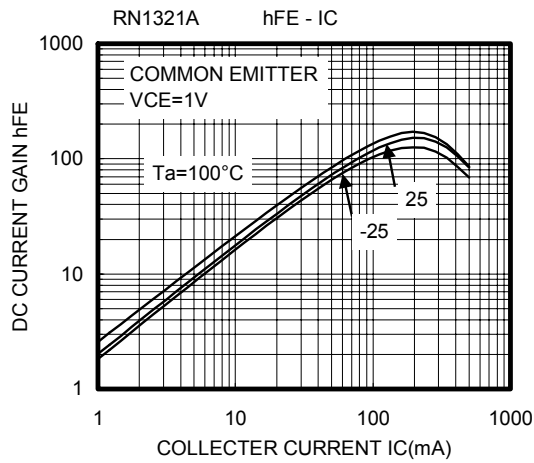
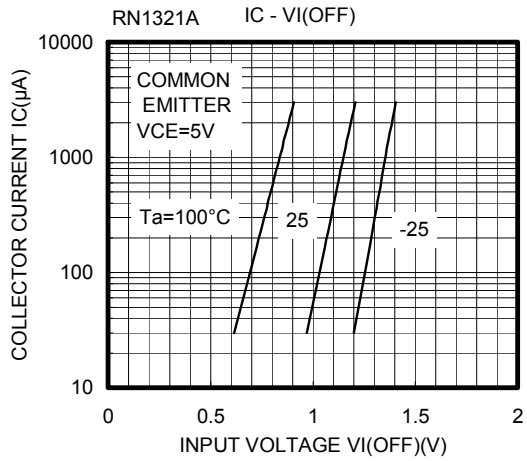
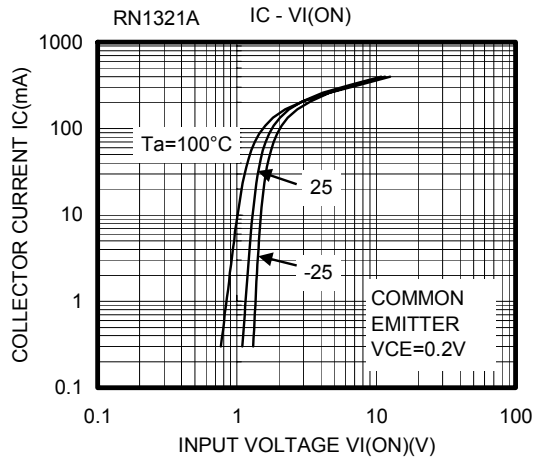


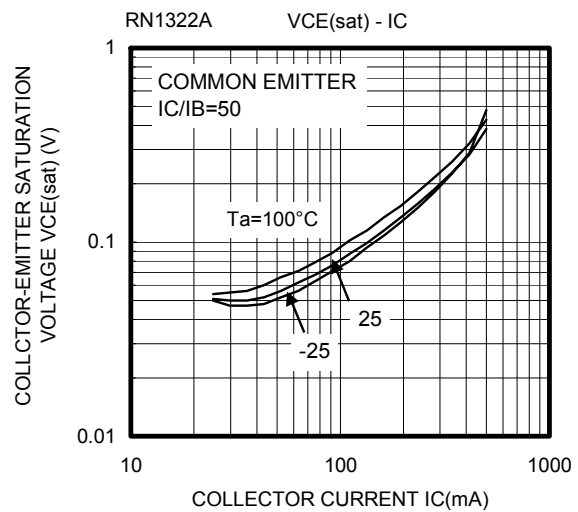
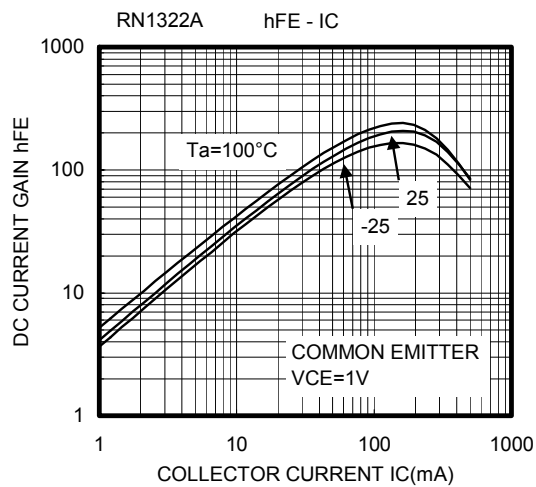
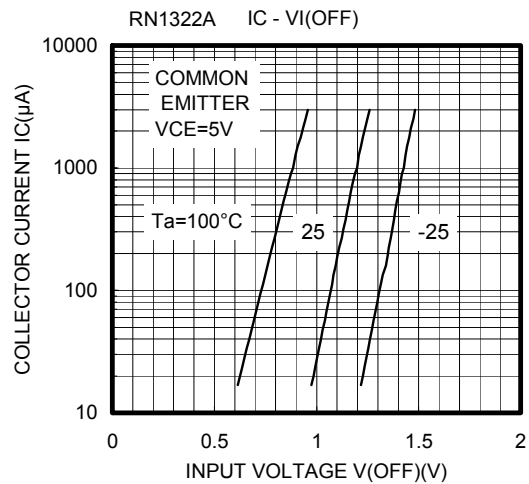
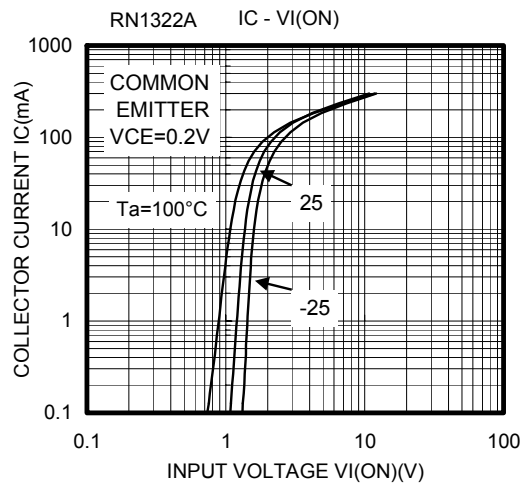
Maximum Ratings ($T_a = 25^\circ\text{C}$)

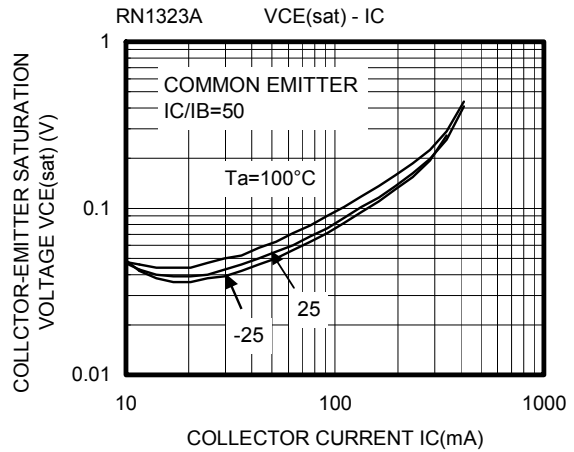
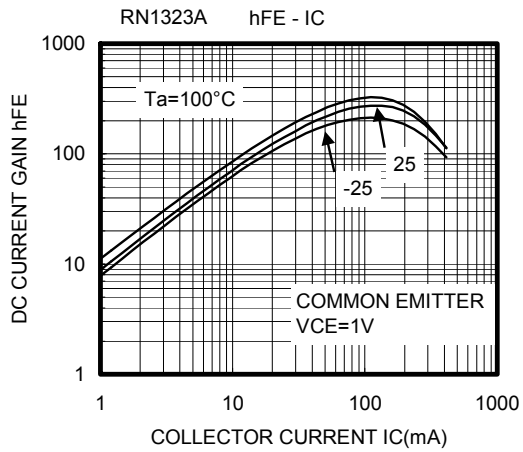
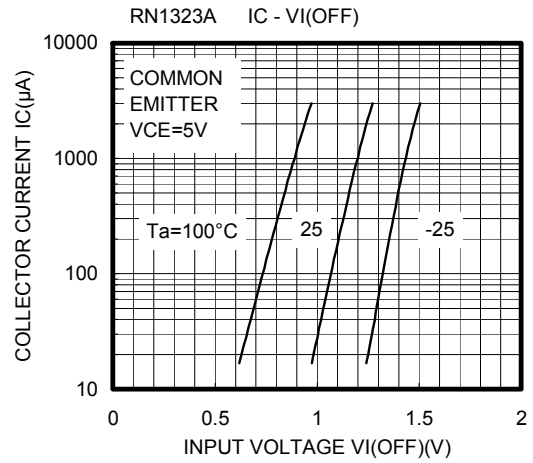
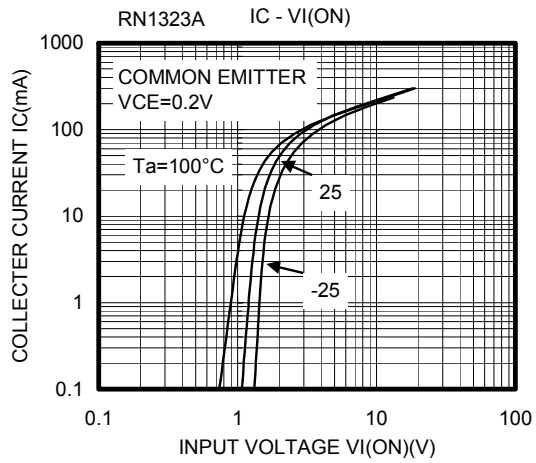
Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	15	V
Collector-emitter voltage	V_{CEO}	12	V
Emitter-base voltage	V_{EBO}	10	V
		5	
		6	
Collector current	I_C	500	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55~150	$^\circ\text{C}$

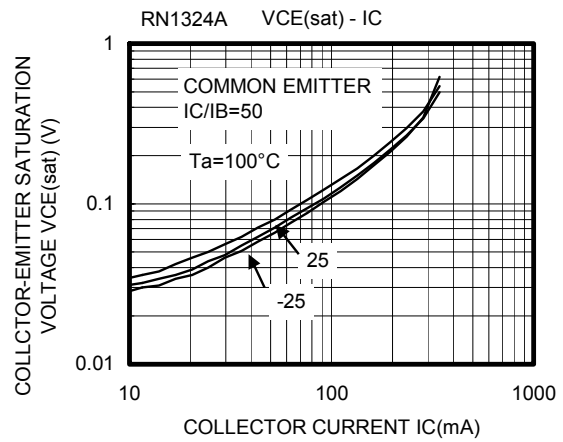
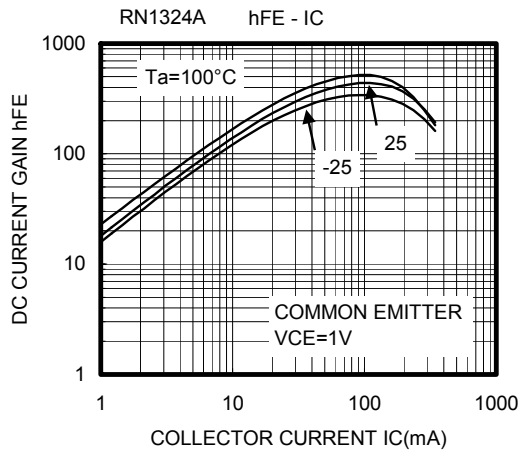
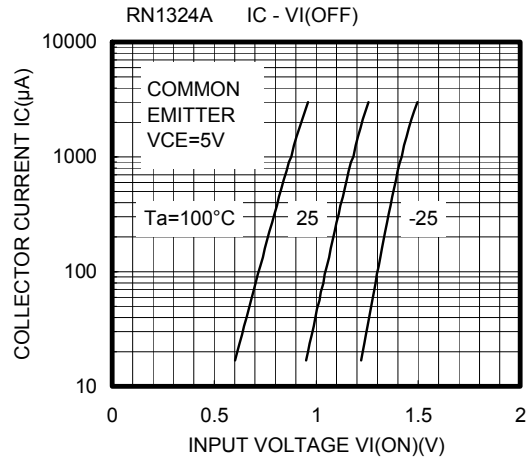
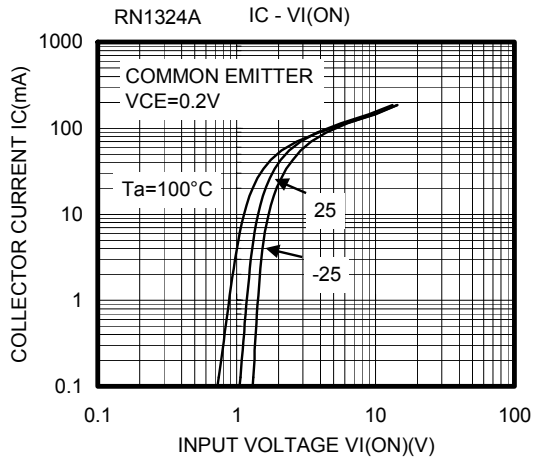
Electrical Characteristics (Ta = 25°C)

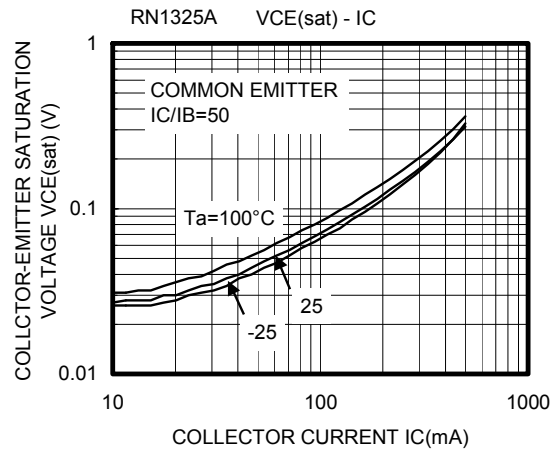
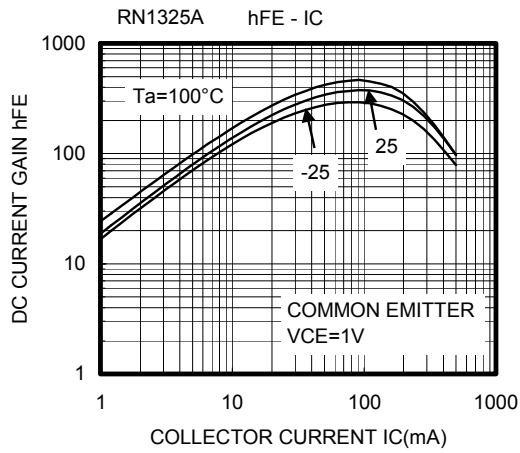
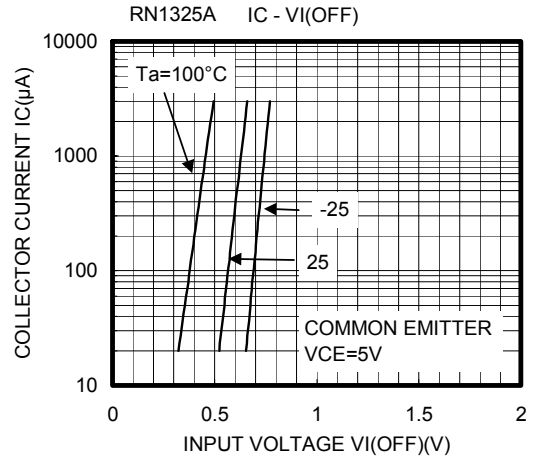
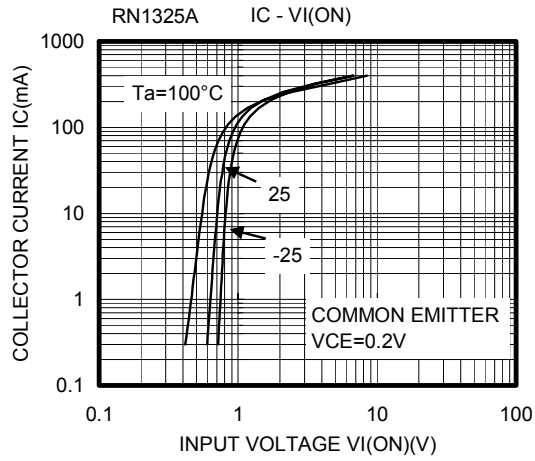
Characteristic		Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	RN1321A~1327A	I_{CBO}	—	$V_{CB} = 15V, I_E = 0$	—	—	100	nA
		I_{CEO}		$V_{CE} = 12V, I_B = 0$	—	—	500	
Emitter cut-off current	RN1321A	I_{EBO}	—	$V_{EB} = 10V, I_C = 0$	3.85	—	7.14	mA
	RN1322A				1.75	—	3.25	
	RN1323A				0.82	—	1.52	
	RN1324A			$V_{EB} = 5V, I_C = 0$	0.38	—	0.71	
	RN1325A				0.365	—	0.682	
	RN1326A				0.35	—	0.65	
	RN1327A			$V_{EB} = 6V, I_C = 0$	0.378	—	0.703	
DC current gain	RN1321A	h_{FE}	—	$V_{CE} = 1V, I_C = 50mA$	35	—	—	
	RN1322A				65	—	—	
	RN1323A				100	—	—	
	RN1324A				140	—	—	
	RN1325A				140	—	—	
	RN1326A				140	—	—	
	RN1327A				140	—	—	
Collector-emitter saturation voltage	RN1321A	$V_{CE(sat)}$	—	$I_C = 50mA, I_B = 2mA$	—	—	0.25	V
	RN1322A~1327A			$I_C = 50mA, I_B = 1mA$				
Input voltage (ON)	RN1321A	$V_{I(ON)}$	—	$V_{CE} = 0.2V, I_C = 50mA$	1.0	—	2.4	V
	RN1322A				1.1	—	2.7	
	RN1323A				1.3	—	3.5	
	RN1324A				1.5	—	5.2	
	RN1325A				0.5	—	1.2	
	RN1326A				0.6	—	1.4	
	RN1327A				0.7	—	1.9	
Input voltage (OFF)	RN1321A~1324A	$V_{I(OFF)}$	—	$V_{CE} = 5V, I_C = 0.1mA$	0.8	—	1.4	V
	RN1325A, 1326A				0.4	—	0.8	
	RN1327A				0.5	—	1.0	
Transition frequency	RN1321A~1327A	f_T	—	$V_{CE} = 5V, I_C = 20mA$	—	300	—	MHz
Collector Output capacitance	RN1321A~1327A	C_{ob}	—	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	4	—	pF
Input resistor	RN1321A	R1	—	—	0.7	1	1.3	kΩ
	RN1322A				1.54	2.2	2.86	
	RN1323A				3.29	4.7	6.11	
	RN1324A				7	10	13	
	RN1325A				0.329	0.47	0.611	
	RN1326A				0.7	1	1.3	
	RN1327A				1.54	2.2	2.86	
Resistor ratio	RN1321A~1324A	R1/R2	—	—	0.85	1.00	1.15	
	RN1325A				0.040	0.047	0.054	
	RN1326A				0.085	0.100	0.115	
	RN1327A				0.187	0.220	0.253	

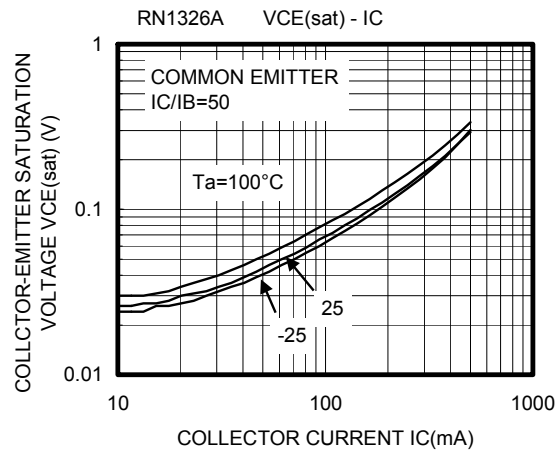
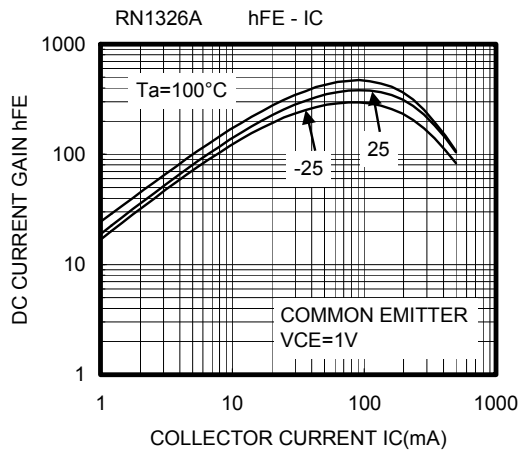
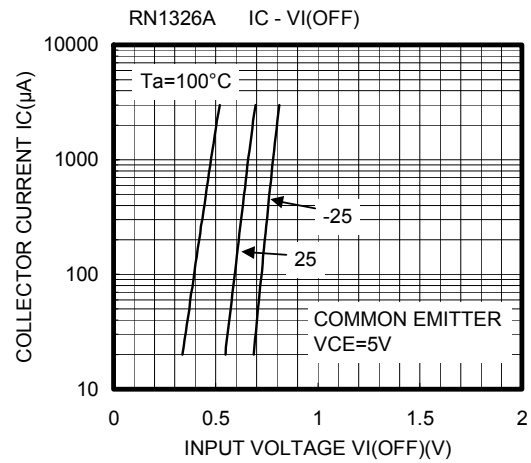
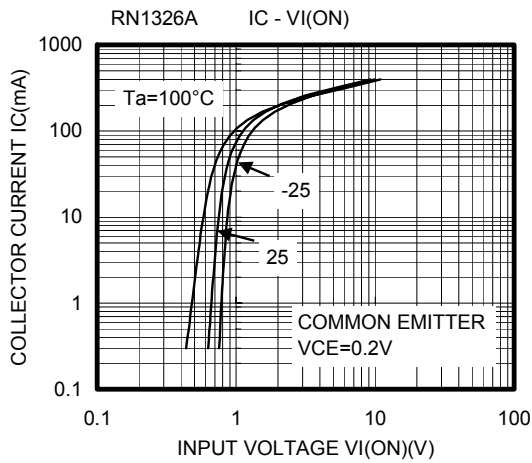


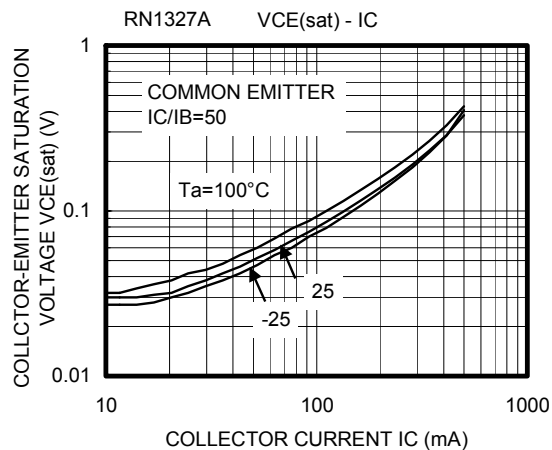
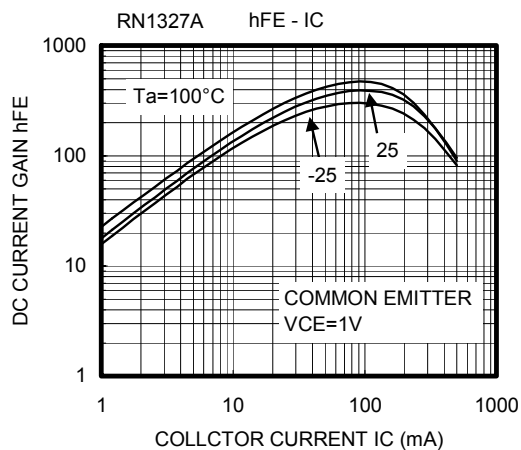
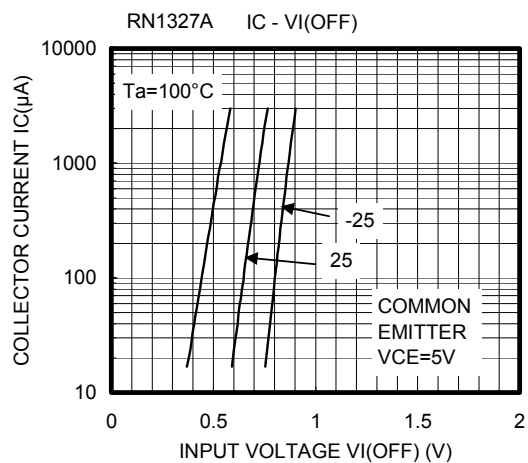
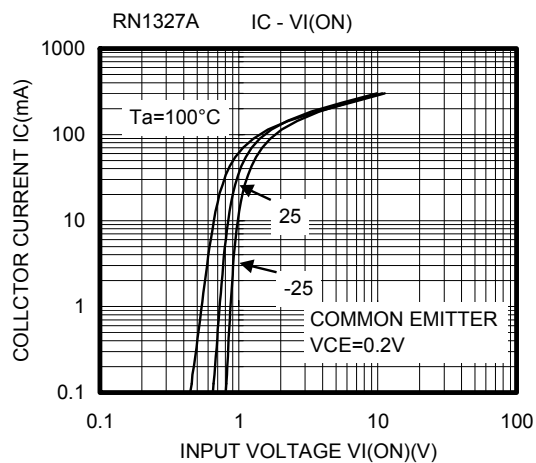


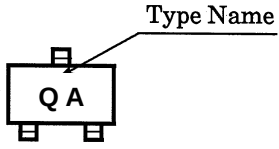
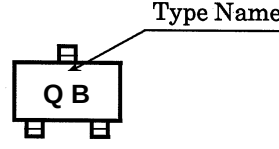
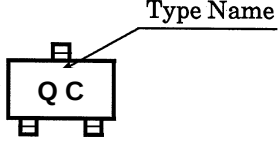
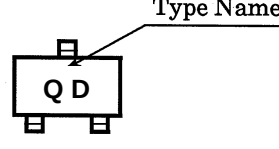
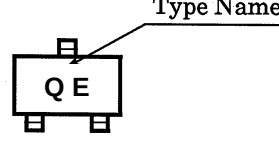
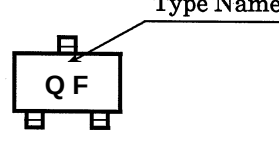
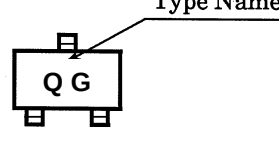










Type Name	Marking
RN1321A	
RN1322A	
RN1323A	
RN1324A	
RN1325A	
RN1326A	
RN1327A	

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